

In the Claims:

Please amend claim 1 as follows:

B1

1. (Twice Amended) A structure formed on a semiconductor substrate comprising:
a plurality of isolation filled trenches in the substrate;
a memory cell including a plurality of holes in the substrate, each having a plurality of sidewalls and a bottom wall, said memory cell located in a region of the semiconductor substrate in which said plurality of isolation filled trenches are absent, said holes having a depth proximate that of said plurality of isolation filled trenches;
insulating material present in each of said plurality of holes on said plurality of sidewalls and bottom wall; and
a conductor overfilling each of said holes and extending onto an adjacent upper surface of the substrate;
wherein said plurality of holes electrically isolate said memory cell from an adjacent memory cell.

Remarks

Applicants respectfully request that this amendment be entered, and that their subject U.S. Patent application be passed to issuance in view thereof. Applicants respectfully submit that the amendments to claim 1 more clearly define Applicants' invention and does not require further search by the Examiner. The foregoing amendments are further indicated in blackline form in Exhibit A, "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

In the Office Action, pending claims 1-5 and 7 stand rejected under 35 U.S.C. 102 in view of the Cunningham reference, U.S. patent 6,177,697 B1 (the '697 patent). In response, Applicants respectfully submit that this reference, taken alone or in combination with any other reference of

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2

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